

CNZ2179

Reflective Photosensor

Overview

CNZ2179 is a reflective photosensor with a long focal distance, in which a high efficiency GaAs infrared light emitting diode is used as a light emitting element and a high sensitivity Si phototransistor is used as the light detecting element.

Features

- Long focal distance : 6 mm (typ.)
- Visible light cutoff resin is used

Absolute Maximum Ratings (Ta = 25°C)

Parameter		Symbol	Ratings	Unit
Input (Light emitting diode)	Reverse voltage (DC)	V _R	3	V
	Forward current (DC)	I _F	50	mA
	Power dissipation	P _D ^{*1}	75	mW
Output (Photo transistor)	Collector current	I _C	20	mA
	Collector to emitter voltage	V _{CEO}	20	V
	Emitter to collector voltage	V _{ECO}	5	V
	Collector power dissipation	P _C ^{*2}	100	mW
Temperature	Operating ambient temperature	T _{opr}	−25 to +80	°C
	Storage temperature	T _{stg}	−30 to +85	°C

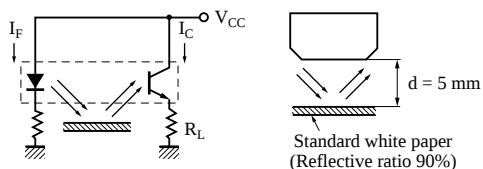
*1 Input power derating ratio is 1.25 mW/°C at Ta ≥ 25°C.

*2 Output power derating ratio is 1.67 mW/°C at Ta ≥ 25°C.

Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Input characteristics	Forward voltage (DC)	V_F $I_F = 50\text{mA}$		1.3	1.5	V
	Reverse current (DC)	I_R $V_R = 3\text{V}$			10	μA
Output characteristics	Collector cutoff current	I_{CEO} $V_{CE} = 10\text{V}$			0.2	μA
Transfer characteristics	Collector current	I_C^{*1} $V_{CC} = 5\text{V}$, $I_F = 20\text{mA}$, $R_L = 100\Omega$	180		1500	μA
	Response time	t_r^{*2} , t_f^{*3} $V_{CC} = 10\text{V}$, $I_C = 0.1\text{mA}$, $R_L = 100\Omega$		20		μs
	Collector to emitter saturation voltage	$V_{CE(sat)}$ $I_F = 50\text{mA}$, $I_C = 0.1\text{mA}$			0.5	V

*1 Transfer characteristics measurement circuit
(Ambient light is shut off completely.)



*2 Time required for the collector current to increase from 10% to 90% of its final value.

*3 Time required for the collector current to decrease from 90% to 10% of its initial value.

